2N4393CSM



MECHANICAL DATA Dimensions in mm (inches) Dimensions in mm (inches) Dimensions in mm (inches) Dimensions in mm (inches)



SMALL SIGNAL N-CHANNEL J-FET IN A HERMETICALLY SEALED CERAMIC SURFACE MOUNT PACKAGE FOR HIGH RELIABILITY APPLICATIONS

FEATURES

- HERMETIC CERAMIC SURFACE MOUNT PACKAGE (SOT23 COMPATIBLE)
- CECC SCREENING OPTIONS
- SPACE QUALITY LEVELS OPTIONS

SOT23 CERAMIC (LCC1 PACKAGE)

Underside View

PAD 1 – Source

PAD 2 – Drain

PAD 3 – Gate

APPLICATIONS:

Hermetically sealed surface mount version of the popular 2N4393 for high reliability / space applications requiring small size and low weight devices.

ABSOLUTE MAXIMUM RATINGS (T_{amb} = 25°C unless otherwise stated)

		-
V _{GD}	Gate – Drain Voltage	-35V
V _{GS}	Gate – Source Voltage	–35V
I _G	Gate Current	50mA
PD	Power Dissipation	350mW
	Derate	2.8mW / °C
Тj	Operating Junction Temperature Range	–55 to 175℃
T _{stg}	Storage Temperature Range	–55 to 175℃
-		

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ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C unless otherwise stated)

	Parameter	Test Conditions		Min.	Тур.	Max.	Unit			
	STATIC CHARACTERISTICS									
V _{(BR)GSS}	Gate – Source Breakdown Voltage	$V_{DS} = 0V$	$I_G = -1\mu A$	-35	-55		V			
V _{GSS(off)}	Gate – Source Cut–off Voltage	$V_{DS} = 20V$	l _D = 1nA	-0.5		-3	v			
I _{DSS*}	Saturation Current	$V_{DS} = 20V$	$V_{GS} = 0V$	5		30	mA			
I _{GSS}	Gate Reverse Current	$V_{GS} = -20V$			-5	-100	pА			
		$V_{DS} = 0V$	T _{amb} = 125℃		-3	-200	nA			
I _{D(off)}	Drain Cut–off Current	$V_{DS} = 20V$	$V_{GS} = -5V$		5	100	pА			
		V _{DS} = 10V	$V_{GS} = -5V$		3	200	nA			
			T _{amb} = 125℃							
V _{DS(on)}	Drain – Source On Voltage	$V_{GS} = 0V$	I _D = 3mA		0.25	0.4	V			
R _{DS(on)}	Drain – Source On Resistance	$V_{GS} = 0V$	I _D = 1mA			100	Ω			
	DYNAMIC CHARACTERISTICS	•								
R _{DS(on)}	Drain – Source On Resistance	$V_{GS} = 0V$	I _D = 0mA			100	0			
		f = 1kHz				100	22			
C _{ISS}	Common – Source Input Capacitance	$V_{DS} = 20V$	V _{GS} = 0V		13	16	pF			
		f = 1MHz			10					
C _{RSS}	Common – Source Reverse Transfer	$V_{DS} = 0V$	$V_{GS} = -5V$		1	5	ъF			
	Capacitance	f = 1MHz			4	5	P			
ē _n	Equivalent Input Noise Voltage	V _{DG} = 10V	I _D = 10mA		3.0		<u>_nV</u>			
		f = 1kHz	Ζ				√Hz			
t _r	Rise Time					5				
t _{d(on)}	Turn-on Time	V _{DD} = 10V	I _D = 3mA			15	nS			
t _f	Fall Time	$V_{GS} = 0V$	$V_{GS(off)} = 5V$			30				
t _{d(off)}	Turn-off Time					50				

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